

Amendments to the Specification

In the Abstract, please amend the following.

~~A vertical trench gate semiconductor device~~ Consistent with an example embodiment, there is a vertical trench gate semiconductor device wherein the trench-gates extend in stripes, the source regions extend transversely between the trench-gates in stripes, projection (20) of the source stripes across the trench-gates defines intermediate trench portions (22) between the projected source stripes, and mutually spaced regions (14,14') of the second conductivity type are provided immediately below the intermediate trench portions (22) which are connected to source potential. The spaced regions serve to selectively shield portions of the trench-gate from the drain region to suppress their contribution to C_{gd} and hence Q_{gd} . In particular, they shield those portions of the trench-gate which do not contribute to the channel width of the device, without restricting the current path where a channel is formed.